Ordering number : ENA1845A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

UD2006FR — Low VF Switching Diode

Diffused Junction Silicon Diode

Features

- V_F=1.4V max. (I_F=20A)
- V_{RRM}=600V
- t_{rr}=60ns (typ.)

Specifications

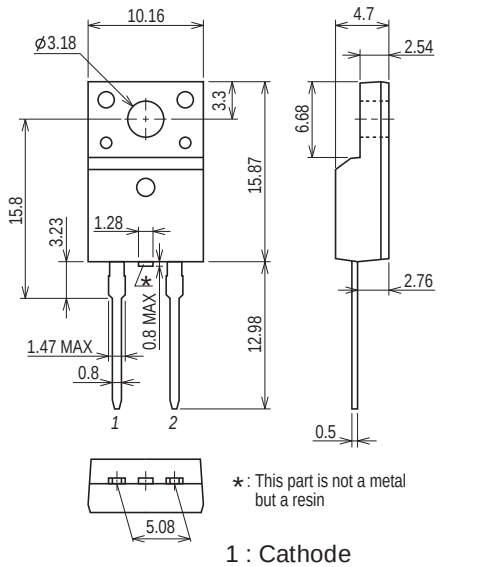
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	DC bias	600	V
Average Output Current	I_O	50Hz resistive load, Sine wave Tc=32℃	20	A
R.M.S Forward Current	I_F(RMS)	Tc=25℃ (SANYO's ideal heat dissipation condition) Package limited, DC	24	A
Surge Forward Current	I_{FSM}	50Hz sine wave 1pulse	180	A
Junction Temperature	Tj		150	℃
Storage Temperature	Tstg		−55 to +150	℃

Package Dimensions

unit : mm (typ)

7532-001



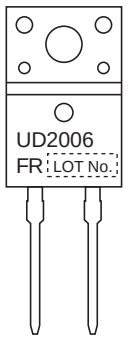
1 : Cathode
2 : Anode

SANYO : TO-220F-2FS

Product & Package Information

- Package : TO-220F-2FS
- JEITA, JEDEC : SC-67
- Minimum Packing Quantity : 50 pcs./magazine

Marking



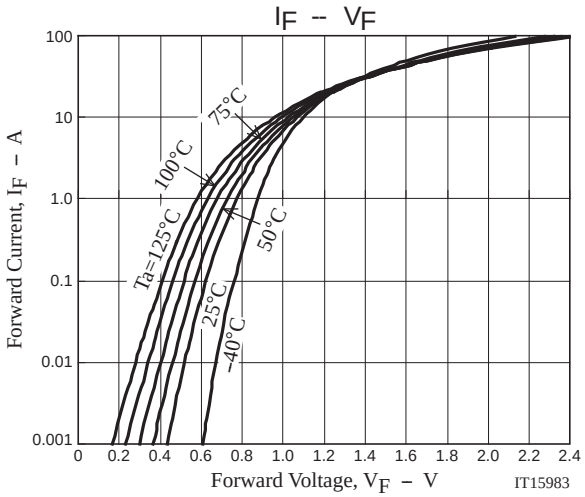
Electrical Connection

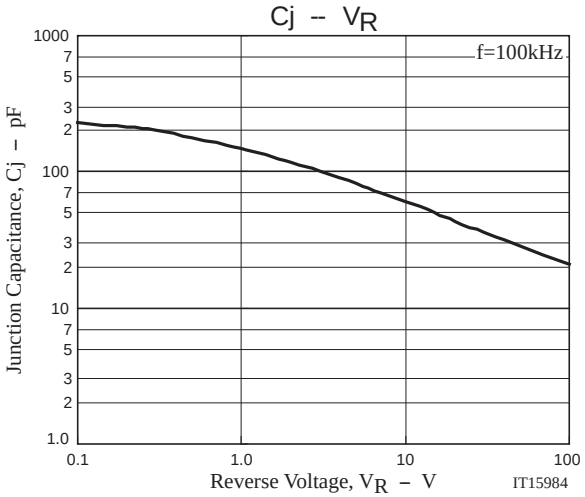
Electrical Characteristics at Ta=25°C

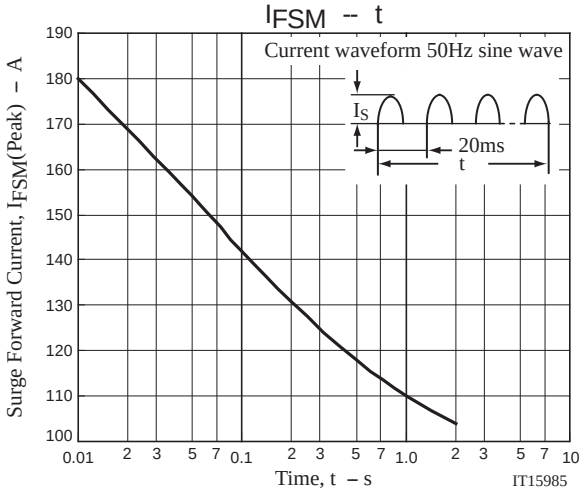
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Voltage	V_R	I_R=1mA	600			V
Forward Voltage	V_F	I_F=20A		1.2	1.4	V
Reverse Current	I_R	V_R=600V			20	μA
Reverse Recovery Time	$t_{rr}1$	I_F=10A, di / dt=100A/μs		75	150	ns
	$t_{rr}2$	I_F=0.5A, I_R=1A		60		ns
Thermal Resistance	Rth(j-c)	Junction -Case : Smoothed DC			4	℃ / W

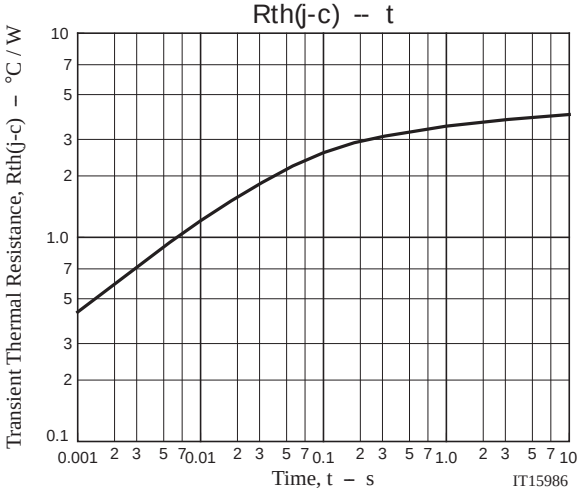
Electrical Characteristics at Ta=125°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Reverse Current	I_R	V_R=600V			200	μA









This catalog provides information as of November, 2011. Specifications and information herein are subject to change without notice.